

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1-13. (Cancelled)

14. (Currently Amended) A method for performing a multi-step etch within a semiconductor-based device processing apparatus, the semiconductor-based device processing apparatus including a barrier having a first position relative to a wafer facilitative of a first etch process and having a second position relative to the wafer facilitative of a second etch process, wherein the wafer is supported by an electrode with a dielectric focus ring with an upper surface and surrounding an outer periphery of the electrode and an outer periphery of the wafer wherein the upper surface of the dielectric focus ring is below an upper surface of the wafer and wherein the barrier is of a dielectric material and surrounds at least part of the focus ring, the method comprising:

performing a first etch process with the barrier in the first position relative to the wafer and the upper surface of the focus ring;

changing the position of the barrier relative to the wafer and the upper surface of the focus ring from the first position relative to the wafer to the second position relative to the wafer; and

performing a second etch process with the barrier in the second position relative to the wafer and the upper surface of the focus ring.

15. (Currently Amended) A method as recited in claim 14 wherein changing the position of the barrier relative to the wafer and the upper surface of the focus ring is performed by moving the barrier.

16. (Original) A method as recited in claim 14 wherein the first etch process is a chemically driven etch.
17. (Original) A method as recited in claim 16 wherein the first etch process is a metal etch.
18. (Original) A method as recited in claim 16 wherein the second etch process is an ion assisted etch.
19. (Original) A method as recited in claim 14 wherein the first etch process is an ion assisted etch.
20. (Original) A method as recited in claim 19 wherein the second etch process is a chemically driven etch.
21. (Original) A method as recited in claim 14 further including a third etch.
22. (Original) A method as recited in claim 21 wherein the third etch occurs between the first and the second etch.
23. (New) A method as recited in claim 15 wherein the moving the barrier moves the barrier until an upper surface of the barrier is not higher than the upper surface of the focus ring.
24. (New) A method as recited in claim 14 further comprising changing the position of the barrier relative to the wafer and the upper surface of the focus ring so that an upper surface of the barrier is not higher than the upper surface of the focus ring.